Quad 2-Input NAND Gate with Schmitt-Trigger Inputs with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT132A is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The MC74HCT132A can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements as Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These are Pb-Free Devices

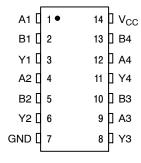


Figure 1. Pin Assignment



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MARKING DIAGRAMS

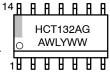


PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A



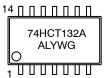


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 F SUFFIX CASE 965



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week
G or • = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Output
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

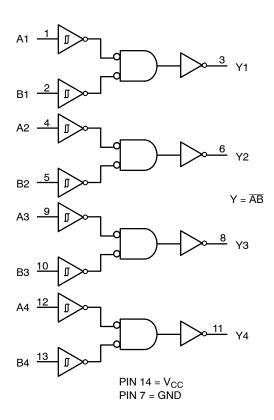


Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT132ANG	PDIP-14 (Pb-Free)	25 / Tape & Ammo Box
MC74HCT132ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HCT132ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HCT132ADTR2G	TSSOP-14*	2500 / Tape & Reel
MC74HCT132AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	Digital Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
lok	Output Diode Current	±20	mA
lout	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
I _{GND}	DC Ground Current per Ground Pin	±75	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance 14-PDIP 14-SOIC 14-TSSOP	78 125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94 V0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	>2000 >100 >500	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A.

- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	-	No Limit (Note 5)	ns

- 5. When V_{IN} ~ 0.5 V_{CC}, I_{CC} >> quiescent current.
 6. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	Guarar	nteed Limit		
Symbol	Parameter	Test Conditions	٧	−55°C to 25°C	≤ 85 °C	≤125°C	Unit
V _{T+} max	Maximum Positive–Going Input Threshold Voltage	$V_{OUT} = 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	1.9 2.1	1.9 2.1	1.9 2.1	V
V _{T+} min	Minimum Positive-Going Input Threshold Voltage	$V_{OUT} = 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	1.2 1.4	1.2 1.4	1.2 1.4	V
V _T _max	Maximum Negative-Going Input Threshold Voltage	$V_{OUT} = V_{CC} - 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	1.2 1.4	1.2 1.4	1.2 1.4	V
V _T _min	Minimum Negative-Going Input Threshold Voltage	$V_{OUT} = V_{CC} - 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	0.5 0.6	0.5 0.6	0.5 0.6	V
V _H min (Note 7)	Minimum Hysteresis Voltage	$V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	0.4 0.4	0.4 0.4	0.4 0.4	V
V _{OH}	Minimum High-Level Output Voltage	$V_{IN} \le V_{T-}$ min or V_{T+} max $ I_{OUT} \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{IN} \le -V_{T-} min \text{ or } V_{T+} max$ $ I_{OUT} \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} \ge V_{T_+} max$ $ I_{OUT} \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	٧
		$V_{IN} \ge V_{T+} max$ $ I_{OUT} \le 4.0 mA$	4.5	0.26	0.33	0.4	
I _{IN}	Maximum Input Leakage Current	V _{IN} = V _{CC} or GND	5.5	± 0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	5.5	1.0	10	40	μΑ

^{7.} $V_H min > (V_{T_+} min) - (V_{T_-} max); V_H max = (V_{T_+} max) + (V_{T_-} min).$

AC ELECTRICAL CHARACTERISTICS (C $_L$ = 50 pF, Input t_f = t_f = 6.0 ns, V_{CC} = 5.0 V \pm 10%)

		V _{CC}	Guaranteed Limit			
Symbol	Parameter	V	−55°C to 25°C	≤ 85 °C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4)	5.0	25	31	38	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	5.0	15	19	22	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (per Gate) (Note 8)	24	pF

^{8.} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

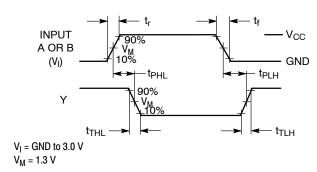
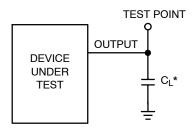


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

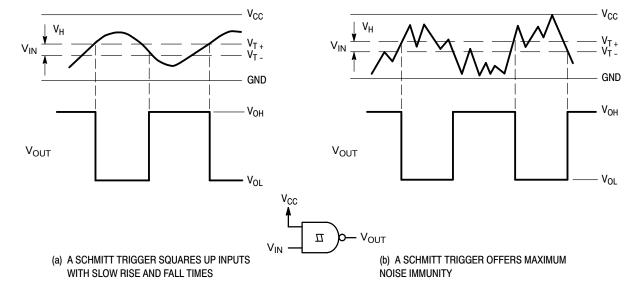
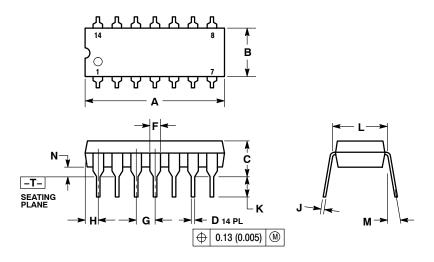


Figure 5. Typical Schmitt-Trigger Applications

PACKAGE DIMENSIONS

PDIP-14 CASE 646-06 ISSUE P

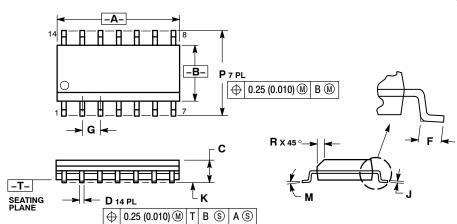


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38	1.01

PACKAGE DIMENSIONS

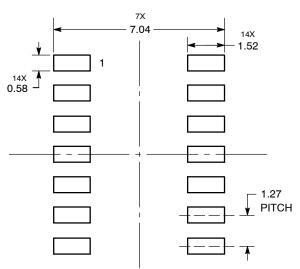
SOIC-14 CASE 751A-03 **ISSUE J**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PEH SIDE.
 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION. CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0°	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

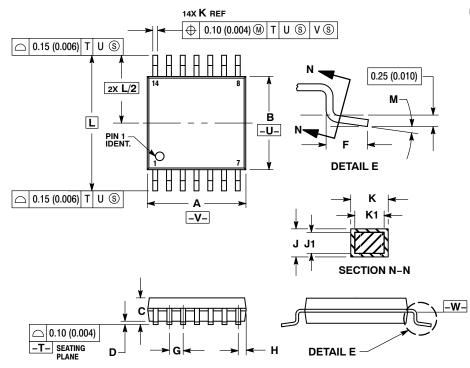


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**

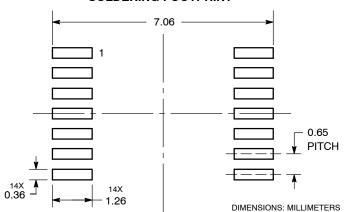


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - DIMENSIONING AND TOLEHANCING PEH ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT
 - EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 - NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 DAWIDAN PHOTHOSION SHALL BE U.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR

 - 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W-.

	MILLIN	IETERS	ERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0 °	8 °	0 °	8 °	

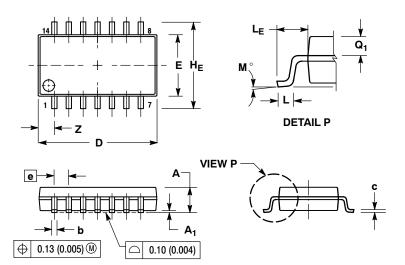
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 **ISSUE B**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. I. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT, MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0°	10°
Q_1	0.70	0.90	0.028	0.035
Z	-	1.42	-	0.056

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